

## 1-Line Bi-directional TVS Diode

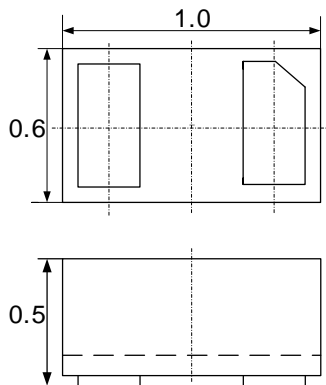
### Description

The FTV0581DFN1006 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The FTV0581DFN1006 complies with the IEC 61000-4-2 (ESD) standard with  $\pm 30\text{kV}$  air and  $\pm 25\text{kV}$  contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD surge protection make FTV0581DFN1006 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

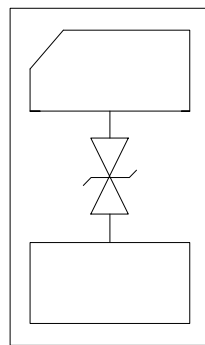
### Mechanical Characteristics

- ◆ Package: DFN1006-2 (1.0 x0.6 x0.5mm)
- ◆ Case Material: "Green" Molding Compound.
- ◆ Moisture Sensitivity: Level 3 per J-STD-020
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

### Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

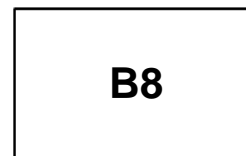
### Features

- ◆ Ultra small package: 1.0 x0.6 x0.5mm
- ◆ Protects one data or power line
- ◆ Ultra low leakage : nA level
- ◆ Operating voltage : 5V
- ◆ Low clamping voltage
- ◆ 2-pin leadless package
- ◆ Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test  
Air discharge:  $\pm 30\text{kV}$   
Contact discharge:  $\pm 25\text{kV}$
  - IEC61000-4-5 (Lightning) 25A (8/20 $\mu\text{s}$ )
- ◆ RoHS Compliant

### Applications

- ◆ Cellular Handsets and Accessories
- ◆ Personal Digital Assistants
- ◆ Notebooks and Handhelds
- ◆ Portable Instrumentation
- ◆ Digital Cameras
- ◆ Peripherals
- ◆ Audio Players
- ◆ Keypads, Side Keys, LCD Displays

### Marking Information



### Ordering Information

Part Number	Marking	Packaging	Reel Size
FTV0581DFN1006	B8	10000/Tape & Reel	7 inch



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### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 $\mu\text{s}$ )	Ppk	300	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	Ipp	25	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	$\pm 30$ $\pm 25$	kV
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

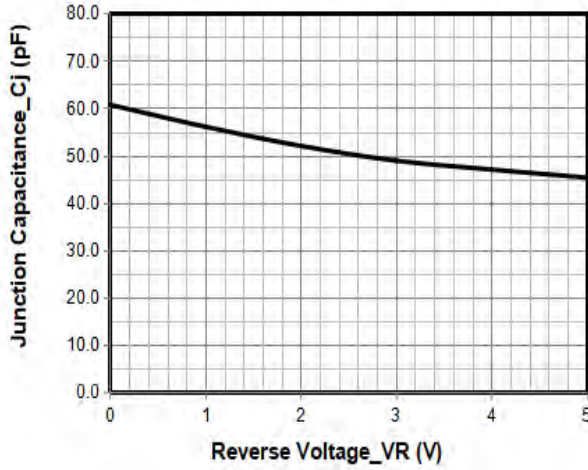
### Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6	7	9	V	IT = 1mA
Reverse Leakage Current	IR			0.2	$\mu\text{A}$	VRWM = 5V
Clamping Voltage	VC			7	V	Ipp = 1A (8 x 20 $\mu\text{s}$ pulse)
Clamping Voltage	VC			12	V	Ipp = 25A (8 x 20 $\mu\text{s}$ pulse)
Junction Capacitance	CJ		60		pF	VR = 0V, f = 1MHz

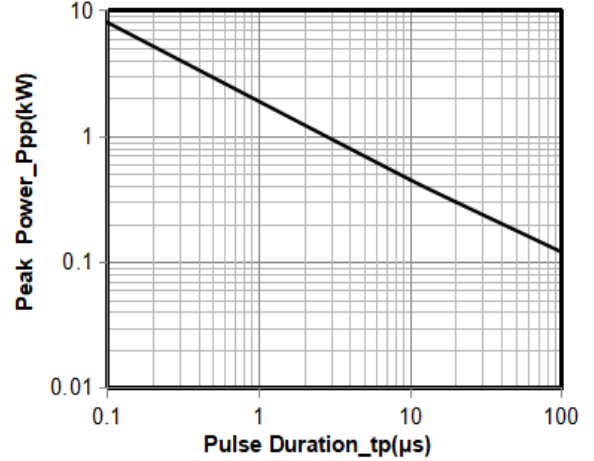


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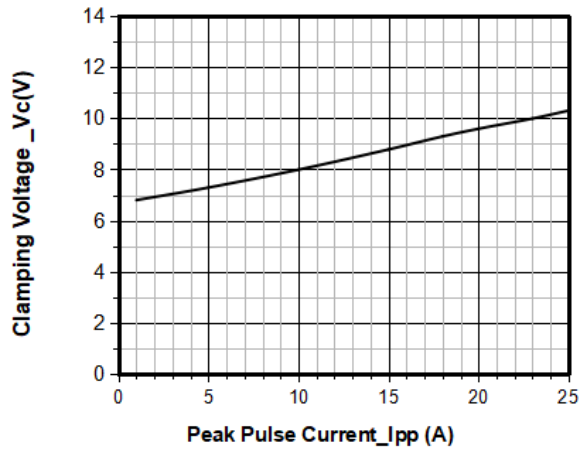
## Typical Performance Characteristics (TA=25°C unless otherwise Specified)



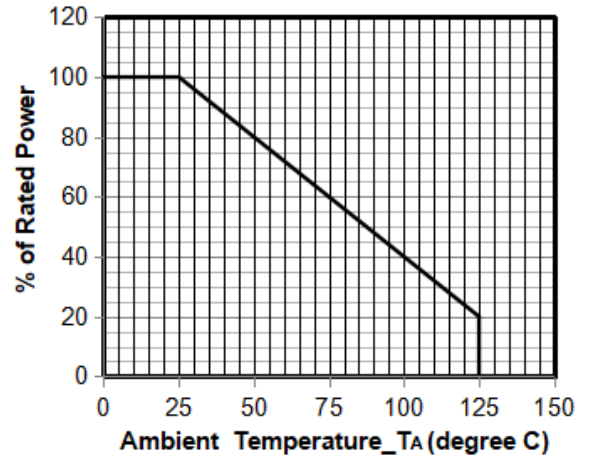
Junction Capacitance vs. Reverse Voltage



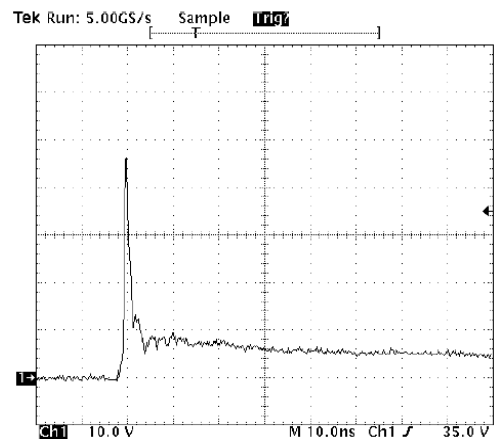
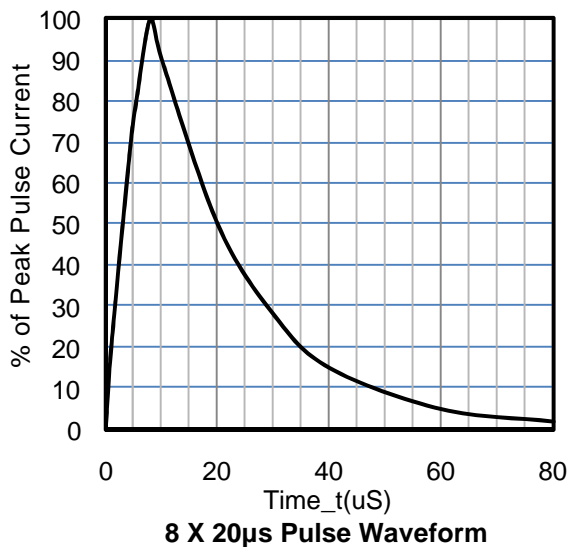
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current



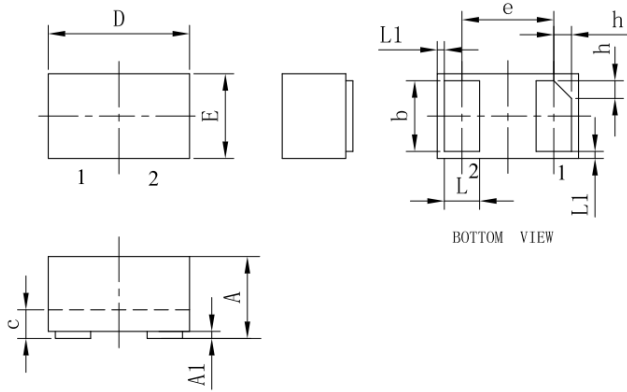
Power Derating Curve



Note : Data is taken with a 10x attenuator  
ESD Clamping Voltage  
8 kV Contact per IEC61000-4-2

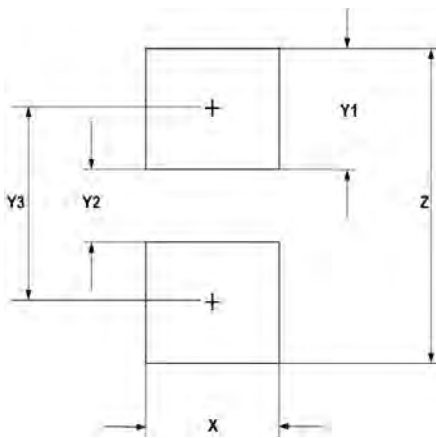
## 1-Line Bi-directional TVS Diode

### DFN1006-2 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.450	0.500	0.550	0.018	0.020	0.022
A1	0.000	0.020	0.050	0.000	0.001	0.002
b	0.450	0.50	0.550	0.018	0.020	0.022
c	0.120	0.150	0.180	0.005	0.006	0.007
D	0.950	1.000	1.050	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05REF			0.002REF		
h	0.07	0.12	0.17	0.003	0.005	0.007

### Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052